

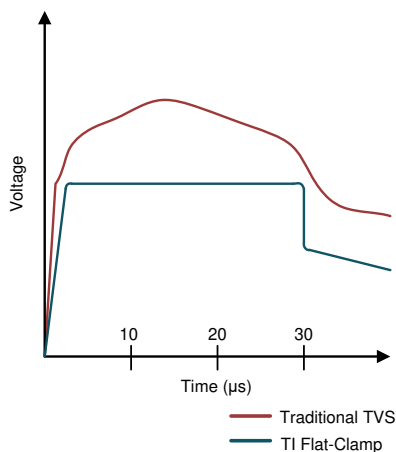
TVS3301 33V 双向平缓钳位浪涌保护器件

1 特性

- 提供功能安全
 - 有助于进行功能安全系统设计的文档
- 保护特性符合针对工业信号线路的 1kV、42 Ω IEC 61000-4-5 浪涌测试要求
- 双向极性可针对双极信号传输或误接线情形提供保护
- 27A 8/20μs
 - 浪涌电流下的钳位电压为 40V
- 关断电压：±33V
- 3mm × 3mm 小型 SON 封装
- 可耐受超过 5,000 次的 25A 8/20μs 浪涌电流的重复冲击
- 强大的浪涌保护
 - IEC61000-4-5 (8/20μs) : 27A
 - IEC61643-321 (10/1000μs) : 3A
- 低泄漏电流
 - 27°C 时的典型值为 2.5nA
 - 85°C 时的最大值为 450nA
- 低电容：54pF
- 集成 4 级 IEC 61000-4-2 ESD 保护

2 应用

- 工业传感器 I/O
- PLC I/O 模块
- 模拟输入
- 电器
- 医疗设备
- 楼宇自动化



对 8/20μs 浪涌事件的电压钳位响应

3 说明

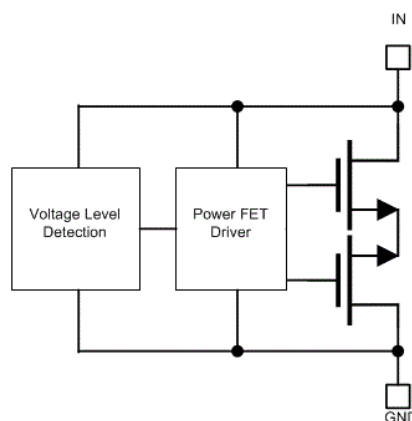
TVS3301 器件可将高达 27A 的 IEC 61000-4-5 故障电流进行分流，以保护系统免受高功率瞬态冲击或雷击。该器件可通过 42 Ω 阻抗进行耦合的方式承受 1kV 的 IEC 61000-4-5 开路电压，满足常见的工业信号线路 EMC 要求。TVS3301 使用反馈机制确保在故障期间发挥精确的平缓钳位能力，使系统接触电压始终低于传统 TVS 二极管。精确的电压调节允许设计人员放心地选择具有较低电压容差的系统组件，从而能够在不影响可靠性的情况下降低系统成本和复杂度。TVS3301 具有 ±33V 的工作范围，可在需要反向接线情形防护的系统中运行。

此外，TVS3301 采用小型 SON 封装，专为空间受限的应用而设计，与标准 SMA 和 SMB 封装相比，其尺寸显著减小。低器件泄露电流和电容确保最大限度地降低了对受保护线路的影响。为了确保在产品的整个寿命期间提供可靠保护，TI 在 125°C 的环境下对 TVS3301 进行了 5000 次重复浪涌冲击测试，但器件性能未发生任何变化。

封装信息^{(1) (2)}

器件型号	封装	封装尺寸 (标称值)
TVS3301	SON (DRB, 8)	3.00mm × 3.00mm

- (1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。
- (2) 有关相关产品，请参阅 [器件比较表](#)。



功能方框图



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4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision A (December 2018) to Revision B (September 2022)	Page
• 更新了整个文档中的表格、图和交叉参考的编号格式.....	1
• 更新了 <i>特性</i> 部分，以添加“提供功能安全型”文本.....	1
Changes from Revision * (September 2018) to Revision A (December 2018)	Page
• 将“预告信息”更改为“量产数据”.....	1

5 说明 (续)

TVS3301 是 TI 的平缓钳位系列浪涌器件中的一款产品。如需深入了解平缓钳位系列，请参阅[用于高效系统保护的平缓钳位浪涌保护技术](#)白皮书。

6 Device Comparison Table

DEVICE	V_{rwm}	V_{clamp} at I_{pp}	I_{pp} (8/20 μs)	Leakage at V_{rwm}	POLARITY	Package
TVS0500	5	9.2 V	43 A	0.07 nA	Unidirectional	DRV (SON-6)
TVS0701	7	11 V	30 A	0.25 nA	Bidirectional	DRB (SON-8)
TVS1400	14	18.6 V	43 A	2 nA	Unidirectional	DRV (SON-6)
TVS1401	14	20.5 V	30 A	1.1 nA	Bidirectional	DRB (SON-8)
TVS1800	18	22.8 V	40 A	0.3 nA	Unidirectional	DRV (SON-6)
TVS1801	18	27.4 V	30 A	0.4 nA	Bidirectional	DRB (SON-8)
TVS2200	22	27.7 V	40 A	3.2 nA	Unidirectional	DRV (SON-6)
TVS2201	22	29.6 V	30 A	2 nA	Bidirectional	DRB (SON-8)
TVS2700	27	32.5 V	40 A	1.7 nA	Unidirectional	DRV (SON-6)
TVS2701	27	34 V	27 A	0.8 nA	Bidirectional	DRB (SON-8)
TVS3300	33	38 V	35 A	19 nA	Unidirectional	DRV (SON-6), YZF (WCSP)
TVS3301	33	40 V	27 A	2.5 nA	Bidirectional	DRB (SON-8)

7 Pin Configuration and Functions

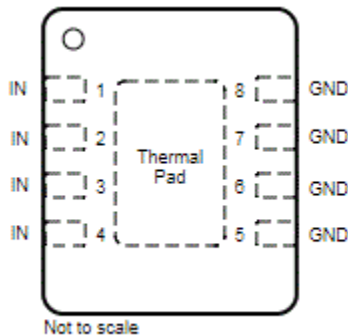


图 7-1. DRB Package,
8-Pin SON
(Top View)

表 7-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	DRB		
IN	1, 2, 3, 4	IN	Surge protected channel
GND	5, 6, 7, 8	GND	Ground
FLOAT	Exposed Thermal Pad	NC	Exposed thermal pad must be floating.

(1) IN = input, GND = ground, NC = no connection.

8 Specifications

8.1 Absolute Maximum Ratings

$T_A = 27^\circ\text{C}$ (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Maximum Surge	IEC 61000-4-5 Current (8/20 μs)		± 27	A
	IEC 61000-4-5 Power (8/20 μs)		1100	W
	IEC 61643-321 Current (10/1000 μs)		± 3	A
	IEC 61643-321 Power (10/1000 μs)		120	W
EFT	IEC 61000-4-4 EFT Protection		± 80	A
I_{BR}	DC Current		20	mA
T_A	Ambient Operating Temperature	-40	125	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65	150	$^\circ\text{C}$

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

8.2 ESD Ratings - JEDEC

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	± 2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	± 500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

8.3 ESD Ratings - IEC

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	IEC 61000-4-2 contact discharge	± 8	kV
		IEC 61000-4-2 air-gap discharge	± 15	

8.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{RWM}	Reverse Stand-Off Voltage		± 33		V

8.5 Thermal Information

THERMAL METRIC ⁽¹⁾		TVS3301	UNIT
		DRB (SON)	
		8 PINS	
R_{qJA}	Junction-to-ambient thermal resistance	52.0	$^\circ\text{C/W}$
$R_{qJC(top)}$	Junction-to-case (top) thermal resistance	56.1	$^\circ\text{C/W}$
R_{qJB}	Junction-to-board thermal resistance	24.9	$^\circ\text{C/W}$
Y_{JT}	Junction-to-top characterization parameter	2.1	$^\circ\text{C/W}$
Y_{JB}	Junction-to-board characterization parameter	24.8	$^\circ\text{C/W}$
$R_{qJC(bot)}$	Junction-to-case (bottom) thermal resistance	9.8	$^\circ\text{C/W}$

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

8.6 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{LEAK}	Leakage Current	Measured at V _{IN} = ±V _{RWM} , T _A = 27°C		2.5	110	nA
		Measured at V _{IN} = ±V _{RWM} , T _A = 85°C			450	
V _{BR}	Break-down Voltage	I _{IN} = ±1 mA	34.4	37.5		V
V _{CLAMP}	Clamp Voltage	±I _{pp} IEC 61000-4-5 Surge (8/20 μs), V _{IN} = 0 V before surge, T _A = 27°C		40	42.5	V
		21 A IEC 61000-4-5 Surge (8/20 μs), V _{IN} = ±V _{RWM} before surge, T _A = 125°C			43.2	
R _{DYN}	8/20 μs surge dynamic resistance	Calculated from V _{CLAMP} at .5*I _{pp} and I _{pp} surge current, T _A = 25°C		35		mΩ
C _{IN}	Input pin capacitance	V _{IN} = V _{RWM} , f = 1 MHz, 30 mV _{pp} , IO to GND		54		pF
SR	Maximum Slew Rate	0-±V _{RWM} rising edge, sweep rise time and measure slew rate when I _{PEAK} = 1 mA, T _A = 27°C		2.5		V/μs
		0-±V _{RWM} rising edge, sweep rise time and measure slew rate when I _{PEAK} = 1 mA, T _A = 85°C		1.0		

8.7 Typical Characteristics

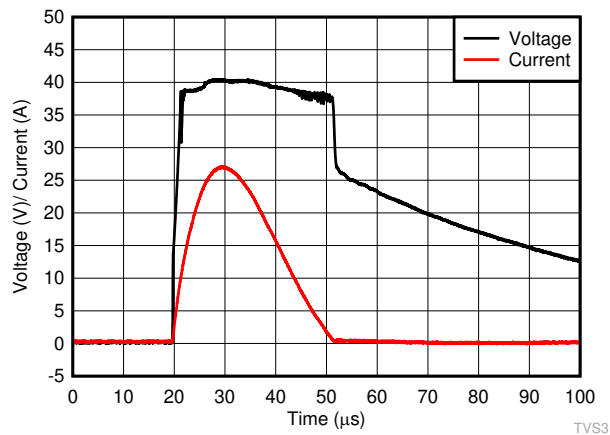


图 8-1. 8/20-μs Surge Response at 27 A

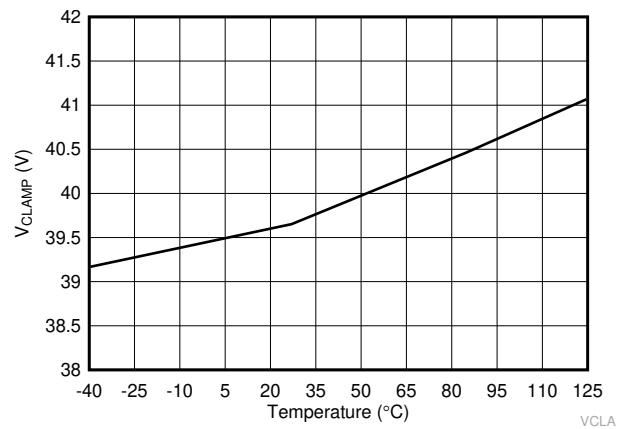
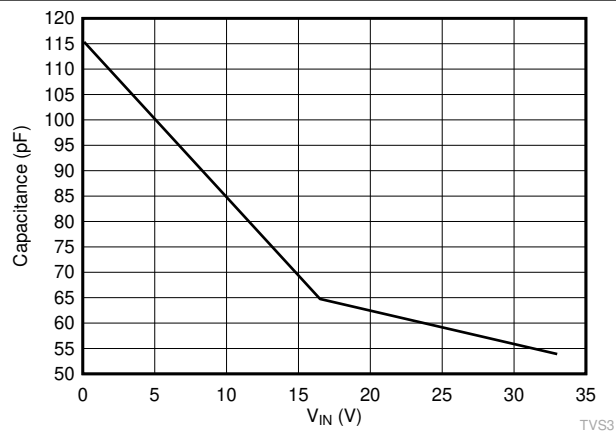


图 8-2. 8/20-μs Surge Clamping Response at 21 A



$f = 1 \text{ MHz}$, 30 mVpp, IO to GND

图 8-3. Capacitance vs Voltage Bias

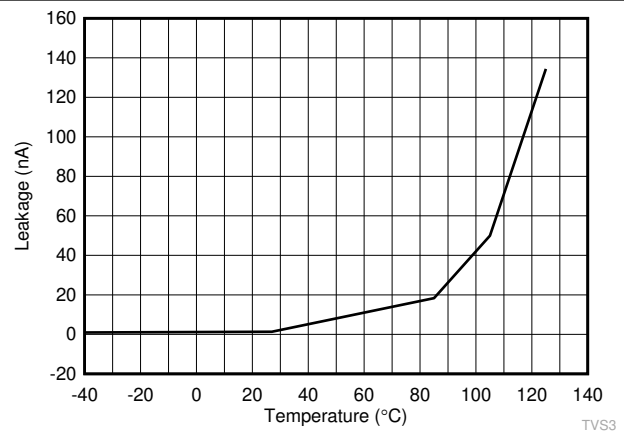


图 8-4. Leakage Current vs Temperature at 33 V

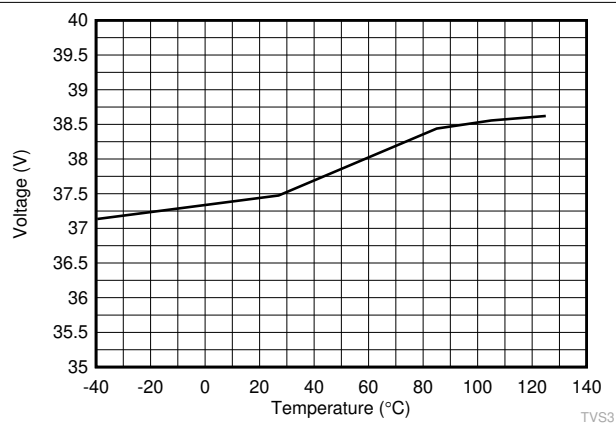


图 8-5. Breakdown Voltage (1 mA) vs Temperature

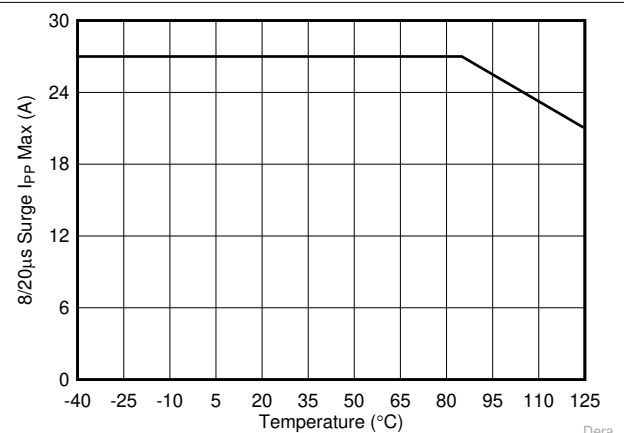


图 8-6. Maximum Surge Current (8/20 μs) vs Temperature

8.7 Typical Characteristics (continued)

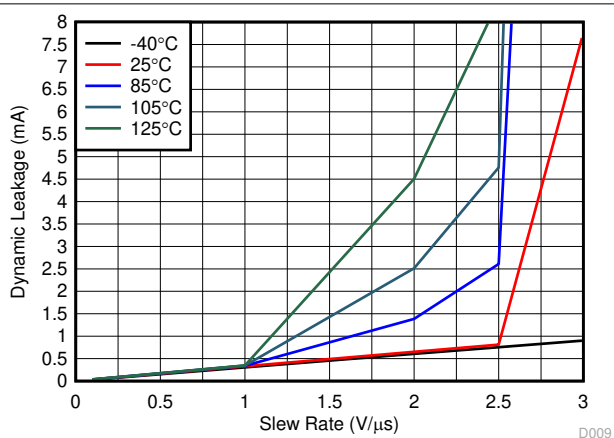


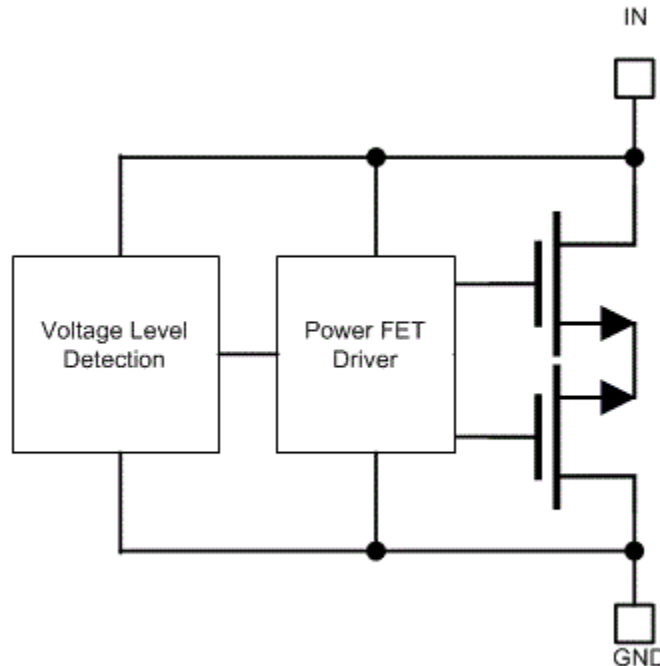
图 8-7. Dynamic Leakage vs Signal Slew Rate Across Temperature

9 Detailed Description

9.1 Overview

The TVS3301 is a bidirectional precision clamp with two integrated FETs driven by a feedback loop to tightly regulate the input voltage during an overvoltage event. This feedback loop leads to a very low dynamic resistance, giving a flat clamping voltage during transient overvoltage events like a surge.

9.2 Functional Block Diagram



9.3 Feature Description

The TVS3301 is a precision clamp that handles 27 A of IEC 61000-4-5 8/20- μ s surge pulse. The flat clamping feature helps keep the clamping voltage very low to keep the downstream circuits from being stressed. The flat clamping feature can also help end-equipment designers save cost by opening up the possibility to use lower-cost, lower voltage tolerant downstream ICs. This device provides a bidirectional operating range, with a symmetrical V_{RWM} of ± 33 V designed for applications that have bipolar input signals or that must withstand reverse wiring conditions. The TVS3301 has minimal leakage at V_{RWM} , designed for applications where low leakage and power dissipation is a necessity. Built-in IEC 61000-4-2 and IEC 61000-4-4 ratings make it a robust protection solution for ESD and EFT events and the TVS3301 wide ambient temperature range of -40°C to $+125^{\circ}\text{C}$ enables usage in harsh industrial environments.

9.4 Device Functional Modes

9.4.1 Protection Specifications

The TVS3301 is specified according to both the IEC 61000-4-5 and IEC 61643-321 standards. This enables usage in systems regardless of which standard is required by relevant product standards or best matches measured fault conditions. The IEC 61000-4-5 standard requires protection against a pulse with a rise time of 8 μ s and a half-length of 20 μ s, while the IEC 61643-321 standard requires protection against a much longer pulse with a rise time of 10 μ s and a half-length of 1000 μ s.

The positive and negative surges are imposed to the TVS3301 by a combination wave generator (CWG) with a 2- Ω coupling resistor at different peak voltage levels. For powered-on transient tests that need power supply bias, inductances are used to decouple the transient stress and protect the power supply. The TVS3301 is post-tested by assuring that there is no shift in device breakdown or leakage at V_{RWM} .

In addition, the TVS3301 has been tested according to IEC 61000-4-5 to pass a ± 1 -kV surge test through a 42- Ω coupling resistor and a 0.5- μ F capacitor. This test is a common test requirement for industrial signal I/O lines and the TVS3301 precision clamp can be used in applications that have that requirement.

The TVS3301 integrates IEC 61000-4-2 level 4 ESD Protection and 80 A of IEC 61000-4-4 EFT Protection. These combine to ensure that the device can protect against most common transient test requirements.

For more information on TI's test methods for Surge, ESD, and EFT testing, refer to the [IEC 61000-4-x Tests for TI's Protection Devices](#) application report.

9.4.2 Reliability Testing

To ensure device reliability, the TVS3301 is characterized against 5000 repetitive pulses of 25-A IEC 61000-4-5 8/20- μ s surge pulses at 125°C. The test is performed with less than 10 seconds between each pulse at high temperature to simulate worst-case scenarios for fault regulation. After each surge pulse, the TVS3301 clamping voltage, breakdown voltage, and leakage are recorded to ensure that there is no variation or performance degradation. By ensuring robust, reliable, high temperature protection, the TVS3301 enables fault protection in applications that must withstand years of continuous operation with no performance change.

9.4.3 Minimal Derating

Unlike traditional diodes, the TVS3301 has very little derating of maximum power dissipation and ensures robust performance up to 125°C, shown in [图 8-6](#). Traditional TVS diodes lose up to 50% of their current carrying capability when at high temperatures, so a surge pulse above 85°C ambient can cause failures that are not seen at room temperature. The TVS3301 prevents this so the designer can see the surge protection regardless of temperature. Because of this, Flat-Clamp devices can provide robust protection against surge pulses that occur at high ambient temperatures, as shown in TI's [TVS Surge Protection in High-Temperature Environments](#) application report.

9.4.4 Bidirectional Operation

The TVS3301 is a bidirectional TVS with a symmetrical operating region. This allows for operation with positive and negative voltages, rather than just positive voltages like the unidirectional TVS3300. This allows for single chip protection for applications where the signal is expected to operate below 0 V or where there is a need to withstand a large common-mode voltage. In addition, there is a system requirement to be able to withstand reverse wiring conditions, in many cases where a high voltage signal is accidentally applied to the system ground and a ground is accidentally applied to the input terminal. This causes a large reverse voltage on the TVS diode that the device must be able to withstand. The TVS3301 is designed to not break down or see failures under reverse wiring conditions for applications that must withstand these miswiring issues.

备注

If the applied signal is not expected to go below 0 V, a unidirectional device will clamp much lower in the reverse direction and should be used. In this case, the recommended device would be the TVS3300.

9.4.5 Transient Performance

During large transient swings, the TVS3301 will begin clamping the input signal to protect downstream conditions. While this prevents damage during fault conditions, it can cause leakage when the intended input signal has a fast slew rate. To keep power dissipation low and remove the chance of signal distortion, TI recommends that the designer keep the slew rate of any input signal on the TVS3301 below 2.5 V/ μ s at room temperature and below 1.0 V/ μ s at 85°C shown in [图 8-7](#). Faster slew rates will cause the device to clamp the input signal and draw current through the device for a few microseconds, increasing the rise time of the signal. This will not cause any harm to the system or to the device, however, it can cause device overheating if the fast input voltage swings occur regularly.

10 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

10.1 Application Information

The TVS3301 can be used to protect any power, analog, or digital signal from transient fault conditions caused by the environment or other electrical components. One common example is using the TVS3301 to protect both sides of a PLC module and a sensor transmitter, as shown in the following figure. The transmitter side of this will be examined in more detail in the following section.

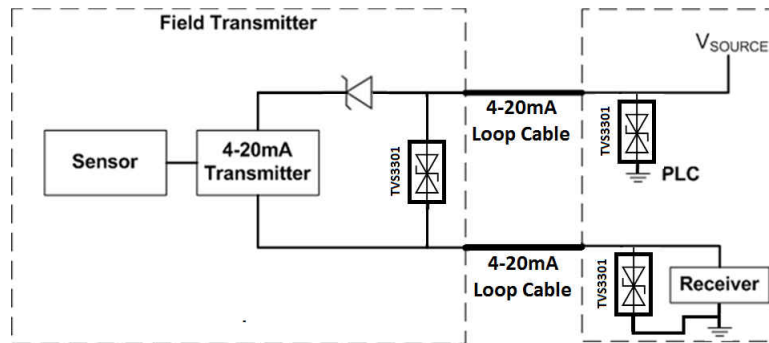


图 10-1. TVS3301 Application Example

10.2 Typical Application

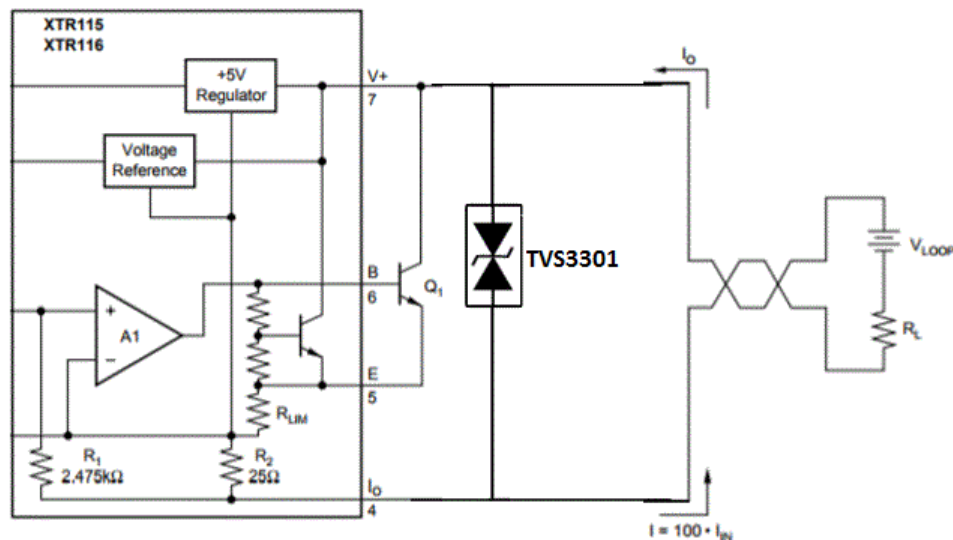


图 10-2. TVS3301 Application Schematic

10.2.1 Design Requirements

A typical operation for the TVS3301 would be protecting an analog output module on a PLC similar to [图 10-2](#). In this example, the TVS3301 is protecting a 4-20 mA transmitter that uses the XTR115, a standard transmitter that has a nominal voltage of 24 V and a maximum input voltage of 40 V. Most industrial interfaces such as this require protection against ± 1 kV surge test through a 42- Ω coupling resistor and a 0.5- μ F capacitor, equaling roughly 24 A of surge current. The system also requires protection from reverse wiring conditions. Without any input protection, this input voltage will rise to hundreds of volts for multiple microseconds, and violate the absolute maximum input voltage and harm the device if a surge event is caused by lightning, coupling, ringing, or any other fault condition. TI's Flat-Clamp technology provides surge protection diodes that can maximize the useable voltage range and clamp at a safe level for the system.

10.2.2 Detailed Design Procedure

If the TVS3301 is in place to protect the device, the voltage will rise to the breakdown of the diode at 37.5 V, during a surge event. The TVS3301 will then turn on to shunt the surge current to ground. With the low dynamic resistance of the TVS3301, large amounts of surge current will have minimal impact on the clamping voltage. The dynamic resistance of the TVS3301 is around 35 m Ω , which means a 24-A surge current will cause a voltage raise of $24 \text{ A} \times 35 \text{ m}\Omega = 0.84 \text{ V}$. Because the device turns on at 37.5 V, this means the XTR115 input will be exposed to a maximum of $37.5 \text{ V} + 0.84 \text{ V} = 38.34 \text{ V}$ during surge pulses, well within the absolute maximum input voltage to ensure robust protection of the circuit.

Because the TVS3301 is a bidirectional device, it also satisfies the condition for withstanding reverse wiring. In this case, if V_{LOOP} is wired in reverse, the input terminal of the TVS3301 will see -24 V , which is below the negative V_{RWM} . The leakages will be the same as if the battery is wired properly.

The small size of the device also improves fault protection by lowering the effect of fault current coupling onto neighboring traces. The small form factor of the TVS3301 allows the device to be placed extremely close to the input connector, which lowers the length of the path fault current going through the system compared to larger protection solutions. Finally, the low leakage of the TVS3301 will have low input power losses. At 33 V, the device will see typical 2.5-nA leakage for a constant power dissipation of less than 100 μ W, a small quantity that will minimally effect overall efficiency metrics and heating concerns.

10.2.3 Application Curves

As shown in [图 10-3](#), the TVS3301 will clamp when exposed to a surge.

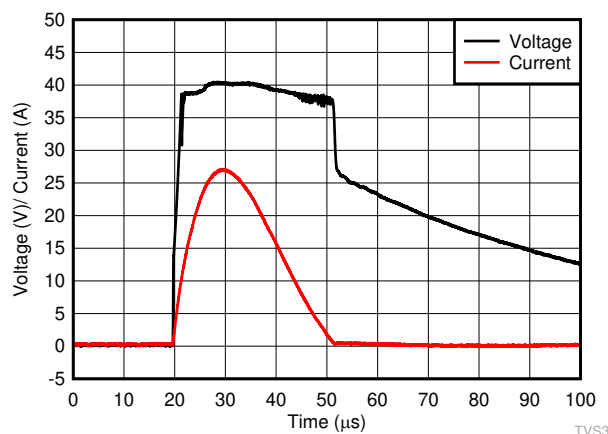


图 10-3. TVS3301 Clamping Waveform (27-A, 8/20- μ s Surge)

10.2.4 PLC Surge Protection Reference Design

For a detailed description of the Flat-Clamp devices advantages in a PLC Analog Input Module, reference TI's [Surge Protection Reference Design for PLC Analog Input Module](#). This document describes the considerations and performance of the TVS3300 in a common industrial application. While the document does not reference the TVS3301 specifically, performance between the devices should be similar.

11 Power Supply Recommendations

The TVS3301 is a clamping device so there is no need to power it. To ensure the device functions properly do not violate the recommended V_{IN} voltage range (– 33 V to 33 V).

12 Layout

12.1 Layout Guidelines

The optimum placement is close to the connector. EMI during an ESD event can couple from the tested trace to other nearby unprotected traces, which could result in system failures. The PCB designer must minimize the possibility of EMI coupling by keeping all unprotected traces away from protected traces between the TVS and the connector. Route the protected traces straight. Use rounded corners with the largest radii possible to eliminate any sharp corners on the protected traces between the TVS3301 and the connector. Electric fields tend to build up on corners, which could increase EMI coupling.

Ensure that the thermal pad on the layout is floating rather than grounded. Grounding the thermal pad will impede the operating range of the TVS3301, and can cause failures when the applied voltage is negative. A floating thermal pad allows the maximum operating range without sacrificing any transient performance.

12.2 Layout Example

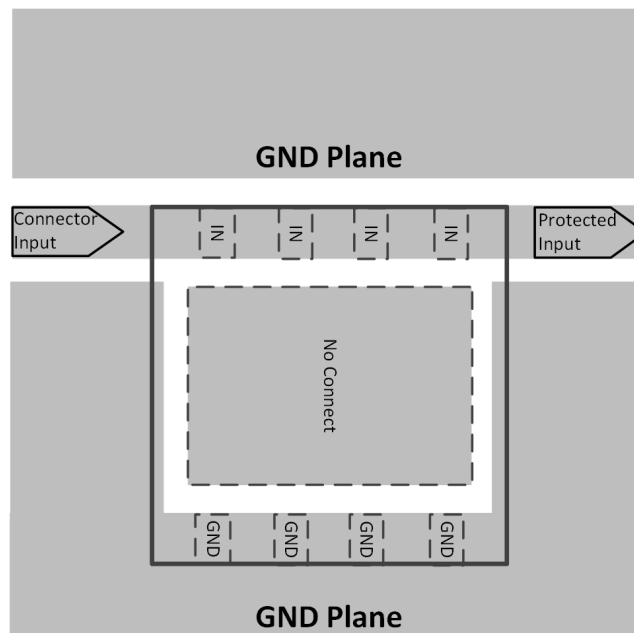


图 12-1. TVS3301 Layout

13 Device and Documentation Support

13.1 Documentation Support

13.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [Flat-Clamp Surge Protection Technology for Efficient System Protection white papers](#)
- Texas Instruments, [IEC 61000-4-x Tests for TI's Protection Devices application reports](#)
- Texas Instruments, [Surge Protection Reference Design for PLC Analog Input Module](#)
- Texas Instruments, [TVS Surge Protection in High-Temperature Environments application reports](#)
- Texas Instruments, [TVS3301 Functional Safety, FIT Rate, Failure Mode Distribution and Pin FMA](#)

13.2 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](https://www.ti.com) 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

13.3 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《[使用条款](#)》。

13.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

所有商标均为其各自所有者的财产。

13.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

13.6 术语表

TI 术语表 本术语表列出并解释了术语、首字母缩略词和定义。

14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TVS3301DRBR	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1PQP
TVS3301DRBR.A	Active	Production	SON (DRB) 8	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1PQP

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TVS3301DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

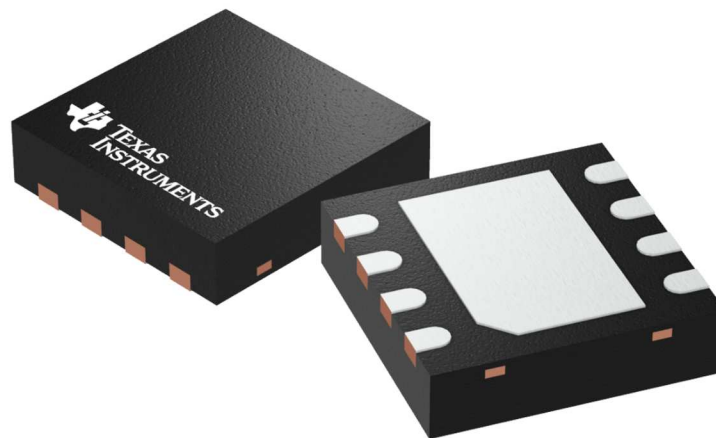
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TVS3301DRBR	SON	DRB	8	3000	338.0	355.0	50.0

DRB 8

GENERIC PACKAGE VIEW

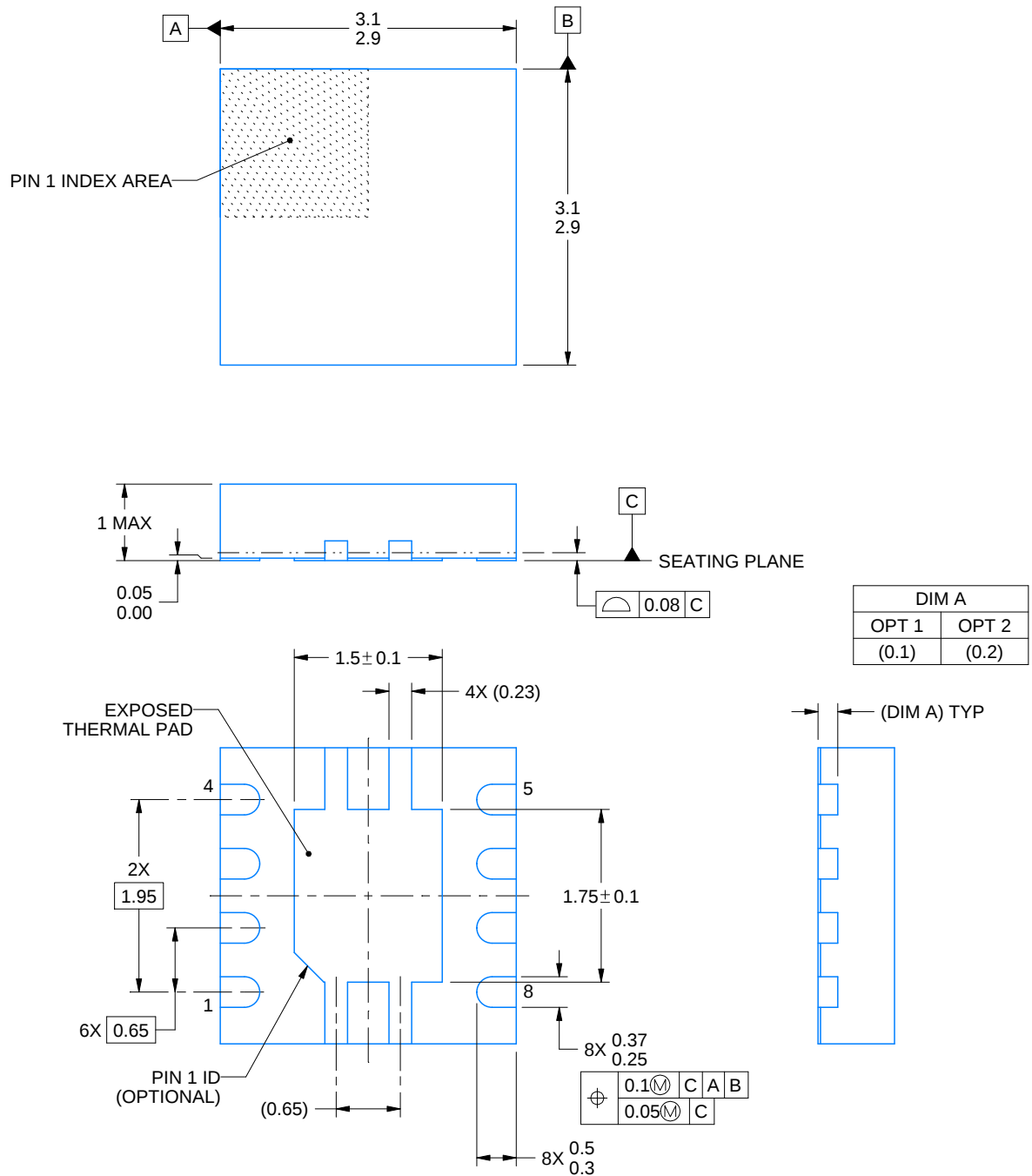
VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4203482/L



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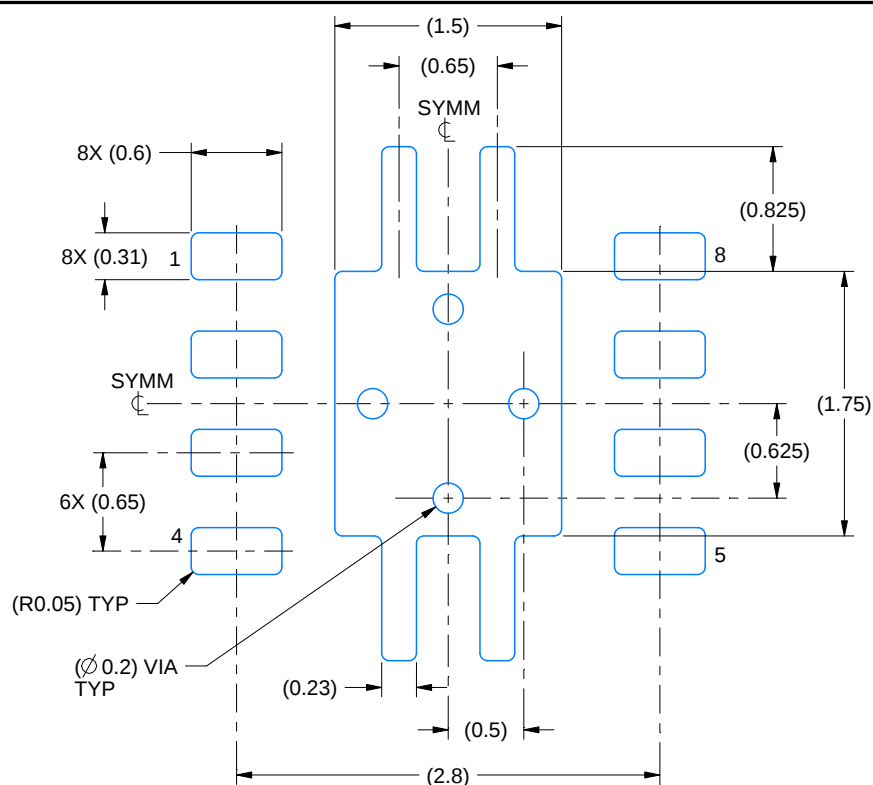
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

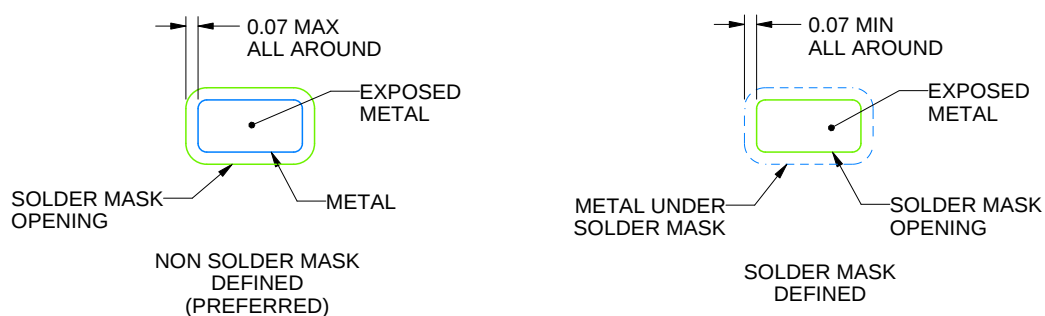
DRB0008A

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:20X



SOLDER MASK DETAILS

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NOTES: (continued)

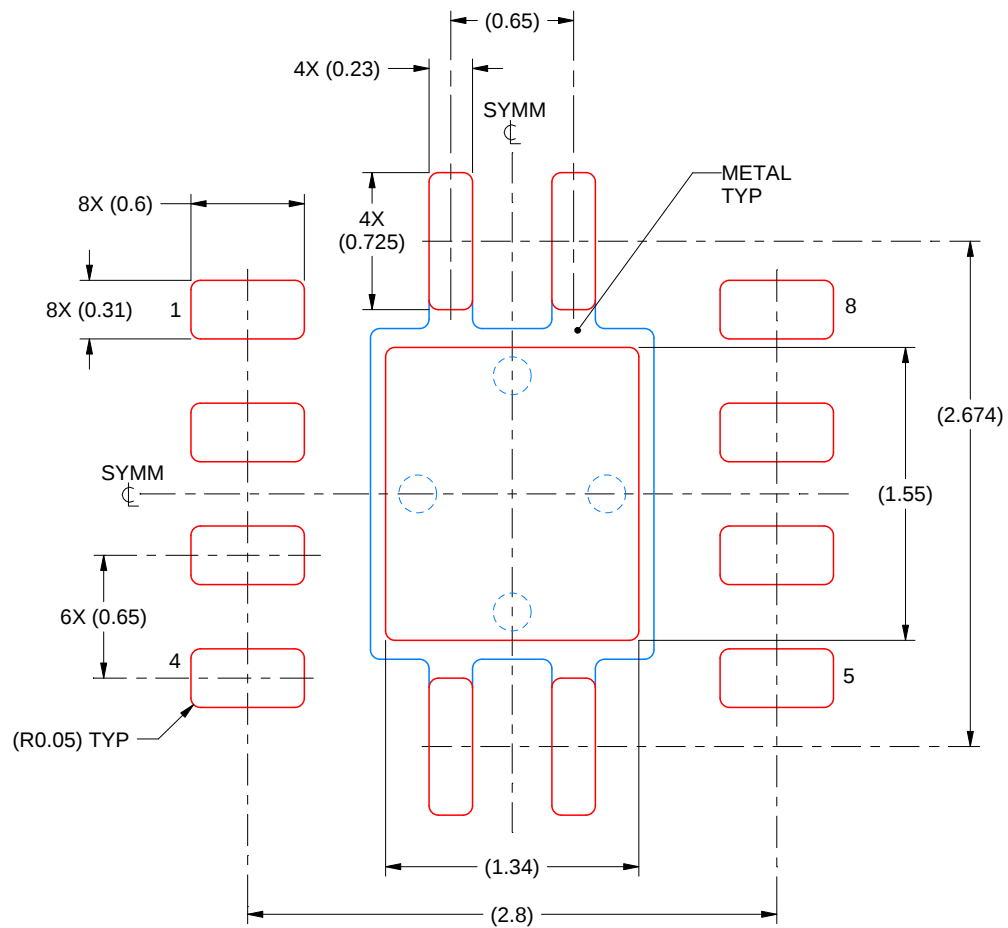
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

DRB0008A

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
84% PRINTED SOLDER COVERAGE BY AREA
SCALE:25X

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NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

重要通知和免责声明

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